

Schottky Diode

30BQ100

100V / 3A

DATASHEET

OEM – International Rectifier

Source: International Rectifier Databook 1995

International Rectifier

PD - 2.441A

30BQ100

SCHOTTKY RECTIFIER

3 Amp

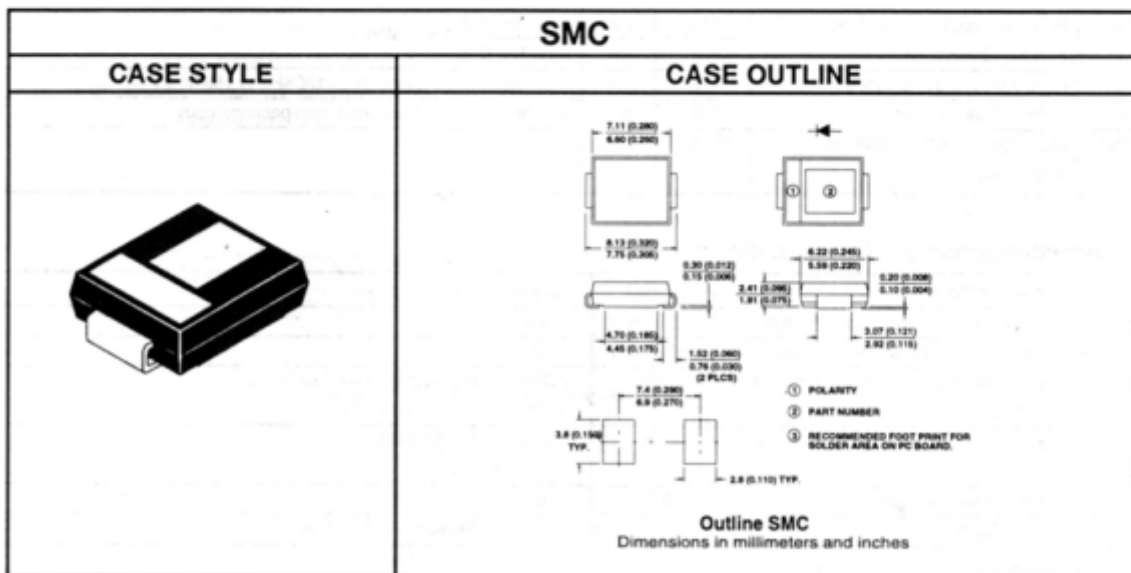
Major Ratings and Characteristics

Characteristics	30BQ100	Units
$I_{F(AV)}$ Rectangular waveform	3.0	A
V_{RRM}	100	V
I_{FSM} @ $t_p = 5\mu s$ sine	2100	A
V_F @ 3.0Apk, $T_J = 125^\circ C$	0.62	V
T_J	-55 to 175	$^\circ C$

Description / Features

The 30BQ100 surface-mount Schottky rectifier has been designed for applications requiring very low forward drop and small foot prints on PC boards. Typical applications are in disk drives, switching power supplies, converters, free-wheeling diodes, battery charging and reverse battery protection.

- Small footprint, surface mountable
- Very low forward voltage drop
- High frequency operation
- Guard ring for enhanced ruggedness and long-term reliability



30BQ100

Voltage Ratings

Part number	30BQ100
V_R Max. DC Reverse Voltage (V)	100
V_{RWM} Max. Working Peak Reverse Voltage (V)	

Absolute Maximum Ratings

Parameters	30BQ	Units	Conditions
$I_{F(AV)}$ Max. Average Forward Current See Fig. 5	3.0	A	50% duty cycle @ $T_C = 143^\circ\text{C}$, rectangular waveform
	4.0		50% duty cycle @ $T_C = 132^\circ\text{C}$, rectangular waveform
I_{FSM} Max. Peak One Cycle Non - Repetitive Surge Current — see Fig. 7	2100	A	5 μs Sine or 3 μs Rect. pulse
	100		10ms Sine or 6ms Rect. pulse
E_{AS} Non - Repetitive Avalanche Energy	50	mJ	$T_J = 25^\circ\text{C}$, $I_{AS} = 2.8\text{A}$, $L = 10\text{mH}$
I_{AR} Repetitive Avalanche Current	2.8	A	Current decaying linearly to zero in 1 μsec Frequency limited by T_J max. $V_A = 1.5 \times V_R$ typical

Electrical Specifications

Parameters	30BQ	Units	Conditions
V_{FM} Max. Forward Voltage Drop See Fig. 1 Ⓞ	0.79	V	@ 3.0A
	0.90	V	@ 6.0A
	0.62	V	@ 3.0A
	0.70	V	@ 6.0A
I_{RM} Max. Reverse Leakage Current Ⓞ See Fig. 2	0.50	mA	$T_J = 25^\circ\text{C}$
	5.0	mA	$T_J = 125^\circ\text{C}$
C_T Max. Junction Capacitance	115	pF	$V_R = 5V_{DC}$, (test signal range 100KHz to 1MHz) 25°C
L_S Typical Series Inductance	3.0	nH	Measured lead to lead 5mm from package body
dv/dt Max. Voltage Rate of Change (Rated V_R)	10,000	V/ μs	

Thermal-Mechanical Specifications

Parameters	30BQ	Units	Conditions
T_J Max. Junction Temperature Range	-55 to 100	$^\circ\text{C}$	
T_{STG} Max. Storage Temperature Range	-55 to 100	$^\circ\text{C}$	
$R_{\theta JA}$ Max. Thermal Resistance, Junction to Ambient	12	$^\circ\text{C}/\text{W}$	DC operation — See Fig. 4
$R_{\theta JL}$ Max. Thermal Resistance, Junction to Lead Ⓜ	46	$^\circ\text{C}/\text{W}$	DC operation
wt Approximate Weight	0.24	g	
Case Style	SMC		Similar to DO-214AB

Ⓞ Pulse Width < 300 μs , Duty Cycle < 2%

Ⓜ Mounted 1 inch square PCB, thermal probe connected to lead 2mm from package

30BQ100

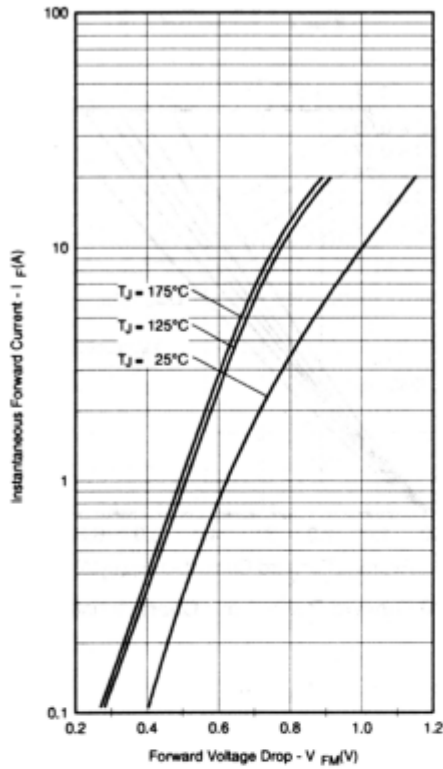


Fig. 1 Max. Forward Voltage Drop Characteristics

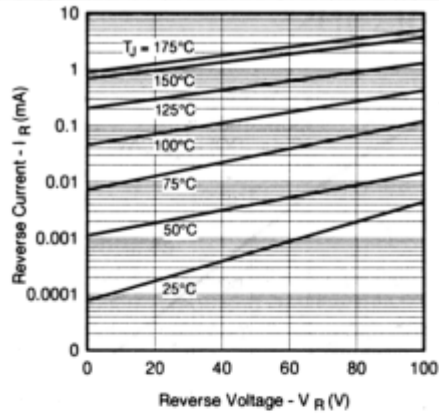


Fig. 2 Typical Values of Reverse Current Vs. Reverse Voltage

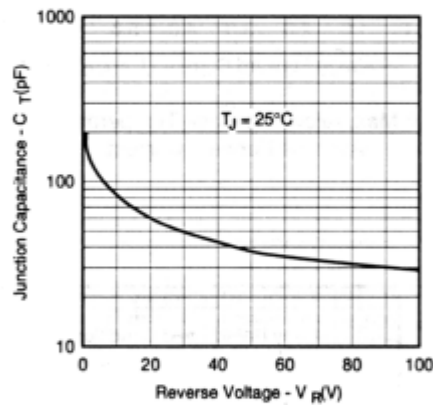


Fig. 3 Typical Junction Capacitance Vs. Reverse Voltage

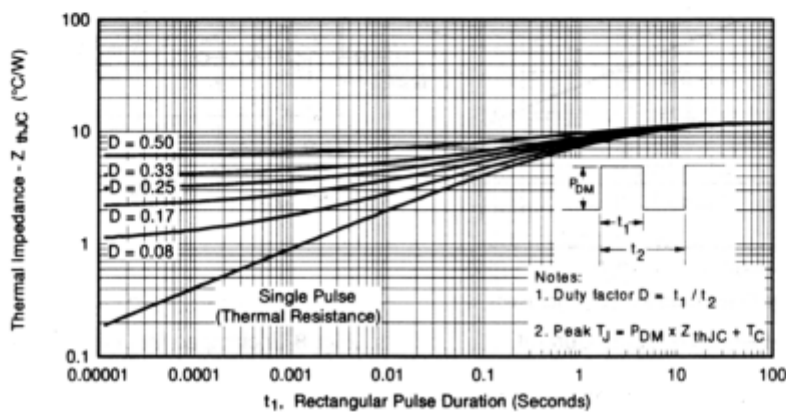


Fig. 4 Max. Thermal Impedance Z_{thJL} Characteristics

30BQ100

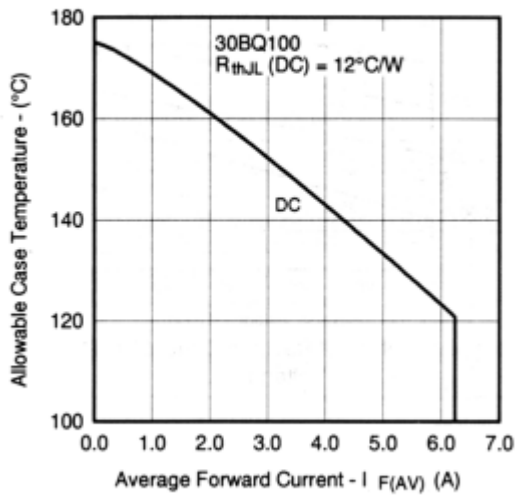


Fig. 5 Max. Allowable Case Temperature Vs. Average Forward Current

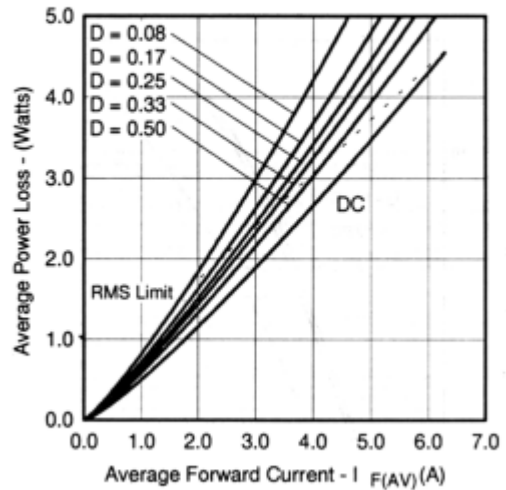


Fig. 6 Forward Power Loss Characteristics

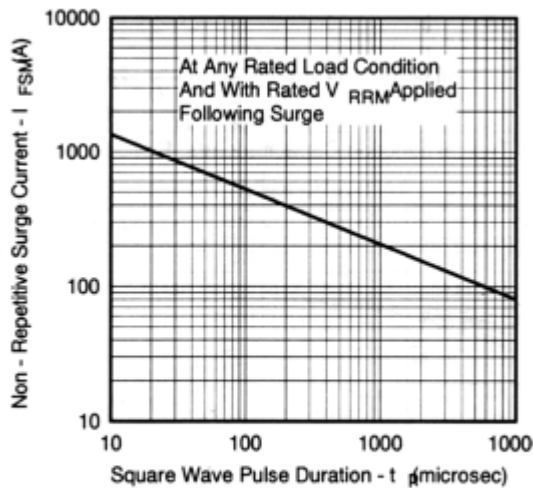


Fig.7 Max. Non-Repetitive Surge Current

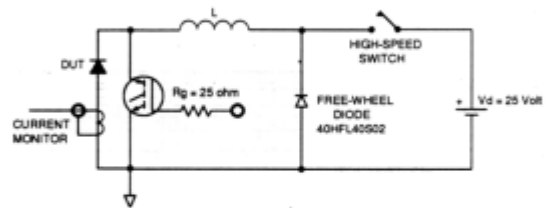


Fig. 8 Unclamped Inductive Test Circuit

Refer to the Appendix Section for the following:
Appendix D: Tape and Reel Information — See page 339.